Analog Power AM7325P

P-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Tv	pical	Apr	olicat	tions:
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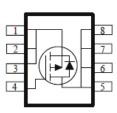
- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)			
-20	7 @ V _{GS} = -4.5V	-18			
-20	10 @ V _{GS} = -2.5V	-15			



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage		V_{DS}	-20	V			
Gate-Source Voltage	V_{GS}	±12	V				
Continuous Drain Current a	T _A =25°C	L	-18				
Continuous Drain Current T _A =		- I _D	-14	Α			
Pulsed Drain Current ^b	I _{DM}	-70					
Continuous Source Current (Diode Conduction) a	I _S	-4.9	Α				
Power Dissipation ^a	T _A =25°C	P_{D}	3.5	W			
Fower Dissipation	T _A =70°C	' D	2	V V			
Operating Junction and Storage Temperature Range	T_J , T_{stg}	-55 to 150	°C				

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec Steady State		35	°C/W			
Maximum Junction-to-Ambient			81	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.5			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	-1 uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	= -16 V, V _{GS} = 0 V, T _J = 55°C		-10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-30			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = -4.5 \text{ V}, I_D = -14.6 \text{ A}$			7	7 mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -11.7 \text{ A}$			10	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -14.6 \text{ A}$		15		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.69		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		90		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = -10 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -14.6 \text{ A}$		9.2			
Gate-Drain Charge	Q_gd	10 = 14.0 A		28			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -10 \text{ V}, R_{L} = 0.7 \Omega,$		20			
Rise Time	t _r	$V_{DS} = -10 \text{ V}, K_L = 0.7 \Omega,$ $I_D = -14.6 \text{ A},$		43		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		238		ns	
Fall Time	t _f	V GEN = 4.0 V, T GEN = 0.12		128			
Input Capacitance	C _{iss}			4665			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		646		pF	
Reverse Transfer Capacitance	C_{rss}			608			

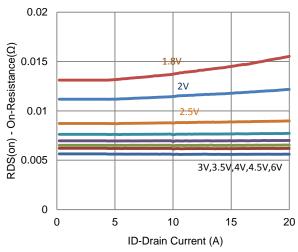
Notes

- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

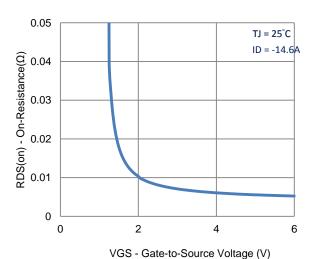
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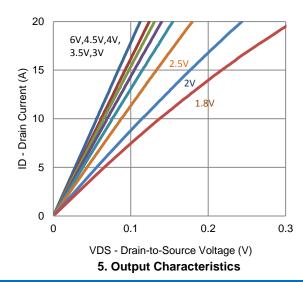
Typical Electrical Characteristics

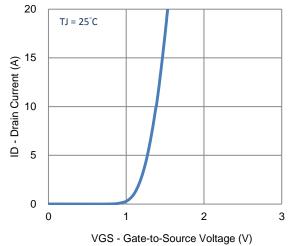


1. On-Resistance vs. Drain Current

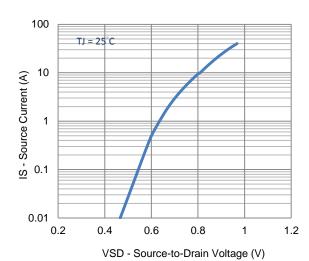


3. On-Resistance vs. Gate-to-Source Voltage

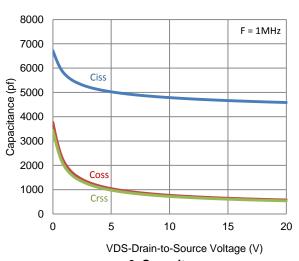




2. Transfer Characteristics



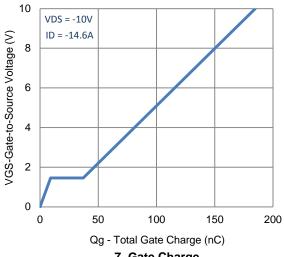
4. Drain-to-Source Forward Voltage

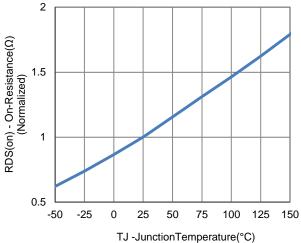


6. Capacitance

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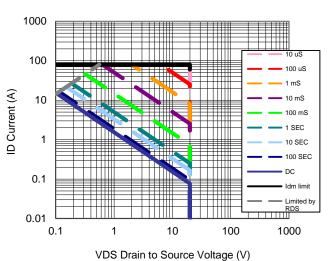
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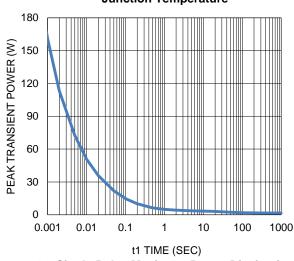




7. Gate Charge

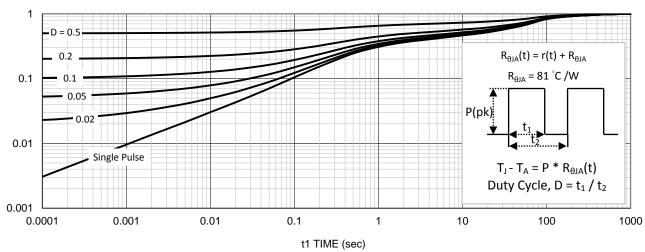






9. Safe Operating Area

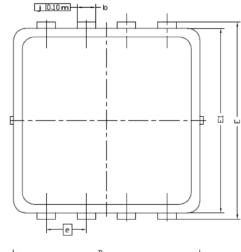
10. Single Pulse Maximum Power Dissipation

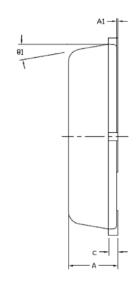


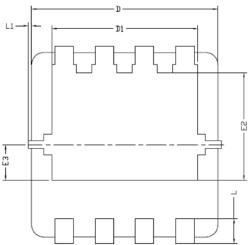
11. Normalized Thermal Transient Junction to Ambient

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Package Information







птм	MILLIMETERS			INCHES			
DIM,	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0'80	0.900	0,0276	0,0315	0.0354	
A1	0.00		0,05	0,000	-	0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2,35 BSC			0.093 BSC			
Ε	3.20 BSC			0,126 BSC			
E1	3.00 B2C			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0.575 BSC			0.023 BSC			
е	0	0.65 BSC		0.026 B2C			
Ĺ	0,30	0,40	0,50	0.0118	0,0157	0.0197	
L1	0		0,100	0		0.004	
91	0°	10°	12°	0°	10°	12°	